

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
 SPRINGFIELD, NEW JERSEY 07081
 U.S.A.

TELEPHONE: (973) 376-2922
 (212) 227-6005
 FAX: (973) 376-8960

Silicon PNP Power Transistor

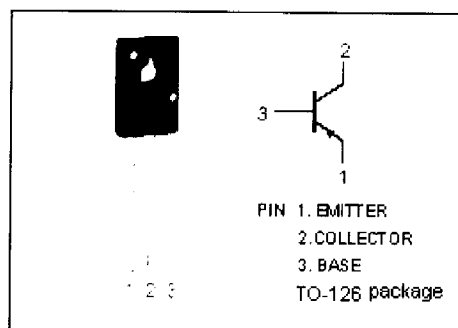
2SA1352

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -200V$ (Min)
- Complement to Type 2SC3416

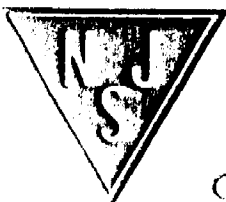
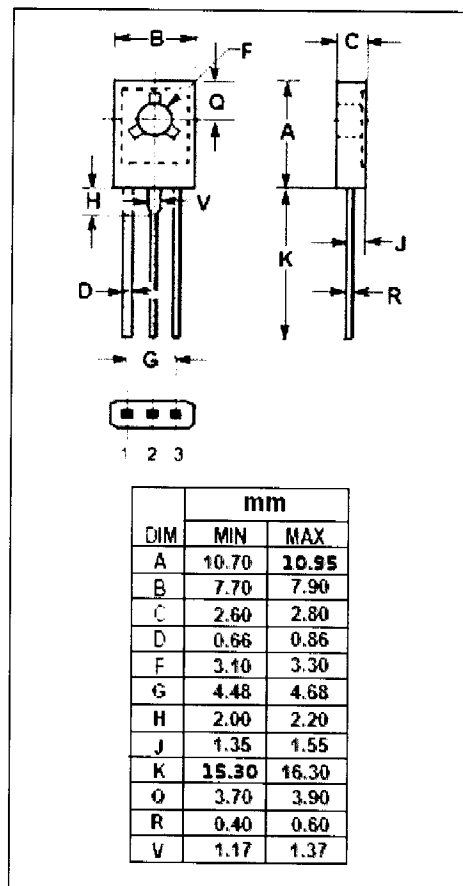
APPLICATIONS

- Designed for color TV chroma output, high-voltage driver applications.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-0.1	A
I_{CM}	Collector Current-Peak	-0.2	A
P_C	Collector Power Dissipation @ $T_a=25^\circ C$	1.2	W
	Total Power Dissipation @ $T_C=25^\circ C$	5	
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Silicon PNP Power Transistor

2SA1352

ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}; I_E = 0$	-200			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; R_{BE} = \infty$	-200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -20\text{mA}; I_B = -2\text{mA}$			-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -20\text{mA}; I_B = -2\text{mA}$			-1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -150\text{V}; I_E = 0$			-0.1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	μA
h_{FE}	DC Current Gain	$I_C = -10\text{mA}; V_{CE} = -40\text{V}$	40		320	
f_T	Current-Gain—Bandwidth Product	$I_C = -10\text{mA}; V_{CE} = -30\text{V}$		70		MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -30\text{V}; f = 1.0\text{MHz}$		1.7		pF

◆ h_{FE} Classifications

C	D	E	F
40-80	60-120	100-200	160-320